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STPS10H100CT/CG/CR/CFP

HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

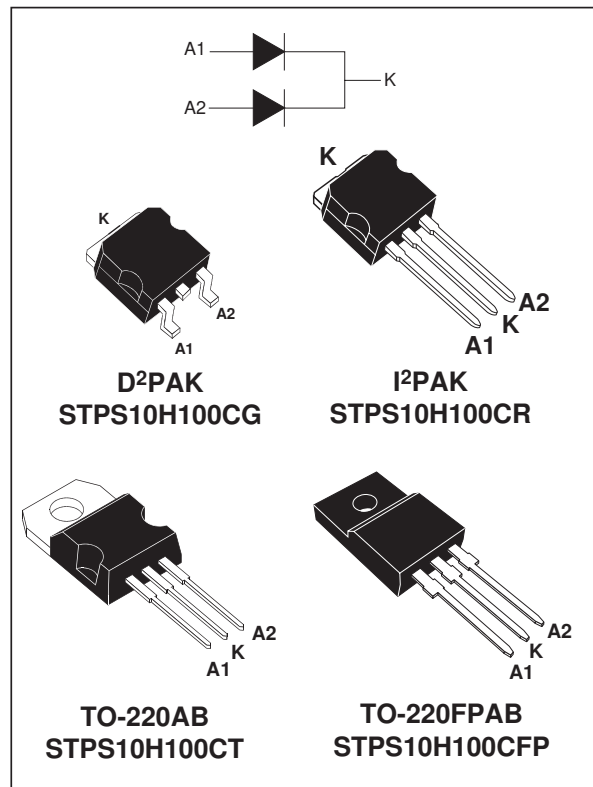
| | |
|-------------|---------|
| $I_{F(AV)}$ | 2 x 5 A |
| V_{RRM} | 100 V |
| T_j | 175°C |
| $V_F(max)$ | 0.61 V |

FEATURES AND BENEFITS

- HIGH JUNCTION TEMPERATURE CAPABILITY FOR CONVERTERS LOCATED IN CONFINED ENVIRONMENT
- LOW LEAKAGE CURRENT AT HIGH TEMPERATURE
- LOW STATIC AND DYNAMIC LOSSES AS A RESULT OF THE SCHOTTKY BARRIER
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Schottky barrier rectifier designed for high frequency miniature Switched Mode Power Supplies such as adaptators and on board DC/DC converters. Packaged in TO-220AB, TO-220FPAB, D²PAK and I²PAK.



ABSOLUTE RATINGS (limiting values, per diode)

| Symbol | Parameter | | | Value | Unit | |
|--------------|--|---|--|---------------|------------------|---|
| V_{RRM} | Repetitive peak reverse voltage | | | 100 | V | |
| $I_{F(RMS)}$ | RMS forward current | | | 10 | A | |
| $I_{F(AV)}$ | Average forward current $\delta = 0.5$ | TO-220AB | $T_c = 165^\circ\text{C}$ | per diode | 5 | A |
| | | D ² PAK / I ² PAK | | | | |
| | | TO-220FPAB | $T_c = 160^\circ\text{C}$ | 10 | | |
| I_{FSM} | Surge non repetitive forward current | | $t_p = 10 \text{ ms}$ sinusoidal | 180 | A | |
| I_{RRM} | Repetitive peak reverse current | | $t_p = 2 \mu\text{s}$ square F = 1kHz | 1 | A | |
| P_{ARM} | Repetitive peak avalanche power | | $t_p = 1 \mu\text{s}$ $T_j = 25^\circ\text{C}$ | 7200 | W | |
| T_{stg} | Storage temperature range | | | - 65 to + 175 | °C | |
| T_j | Maximum operating junction temperature * | | | 175 | °C | |
| dV/dt | Critical rate of rise of reverse voltage | | | 10000 | V/ μs | |

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

THERMAL RESISTANCES

| Symbol | Parameter | | Value | Unit | |
|----------------------|------------------|---------------------------|-----------|------|------|
| R _{th(j-c)} | Junction to case | D2PAK / I2PAK TO-220AB | Per diode | 2.2 | °C/W |
| | | | Total | 1.3 | |
| R _{th(c)} | | | Coupling | 0.3 | |
| R _{th(j-c)} | Junction to case | TO-220FPAB | Per diode | 4.5 | °C/W |
| | | | Total | 3.5 | |
| R _{th(c)} | | | Coupling | 2.5 | |

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

| Symbol | Parameter | Tests conditions | | Min. | Typ. | Max. | Unit |
|-------------------|-------------------------|------------------------|-----------------------------------|------|------|------|------|
| I _R * | Reverse leakage current | T _j = 25°C | V _R = V _{RRM} | | | 3.5 | µA |
| | | T _j = 125°C | | | 1.3 | 4.5 | mA |
| V _F ** | Forward voltage drop | T _j = 25°C | I _F = 5 A | | | 0.73 | V |
| | | T _j = 125°C | | | 0.57 | 0.61 | |
| | | T _j = 25°C | I _F = 10 A | | | 0.85 | |
| | | T _j = 125°C | | | 0.66 | 0.71 | |

Pulse test : * tp = 5 ms, δ < 2%

** tp = 380 µs, δ < 2%

To evaluate the maximum conduction losses use the following equation :

$$P = 0.51 \times I_{F(AV)} + 0.02 \times I_{F(RMS)}^2$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

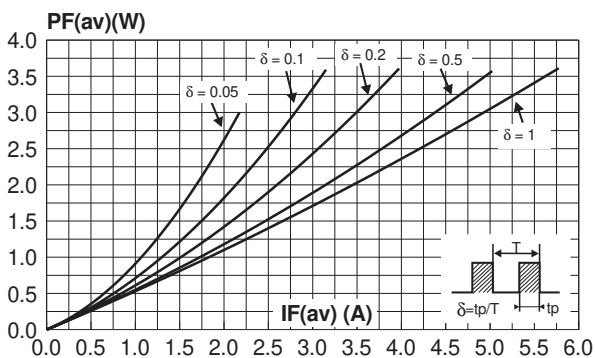


Fig. 2: Average forward current versus ambient temperature (δ=0.5, per diode).

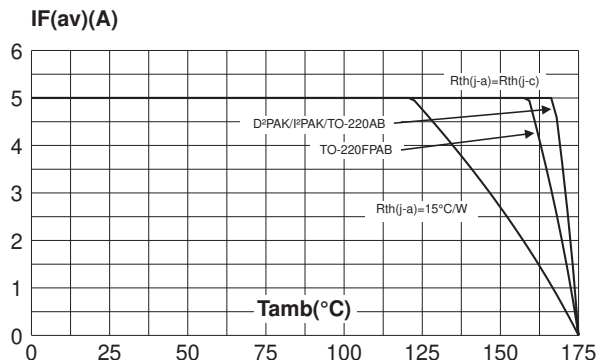


Fig. 3: Normalized avalanche power derating versus pulse duration.

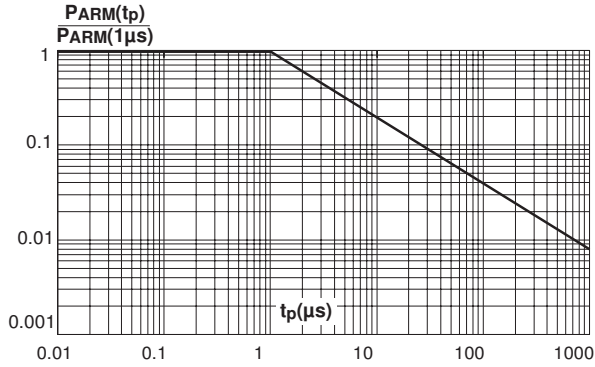


Fig. 4: Normalized avalanche power derating versus junction temperature.

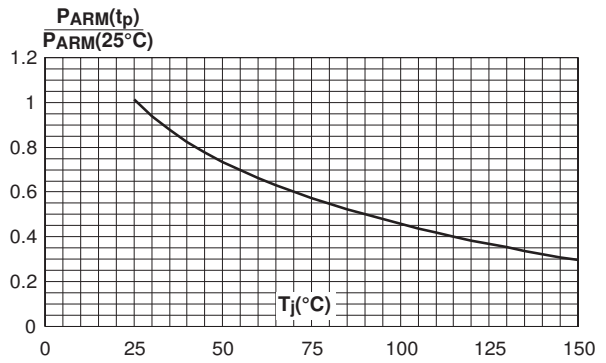


Fig. 5-1: Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

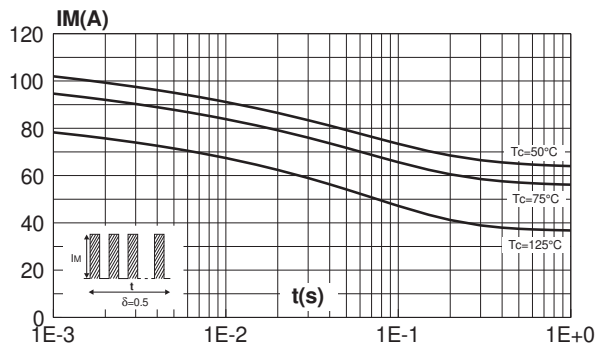


Fig. 5-2: Non repetitive surge peak forward current versus overload duration (maximum values, per diode)(TO-220FPAB)

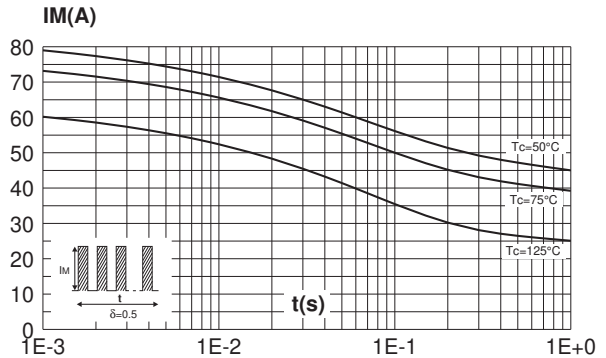


Fig. 6-1: Relative variation of thermal impedance junction to case versus pulse duration (per diode).

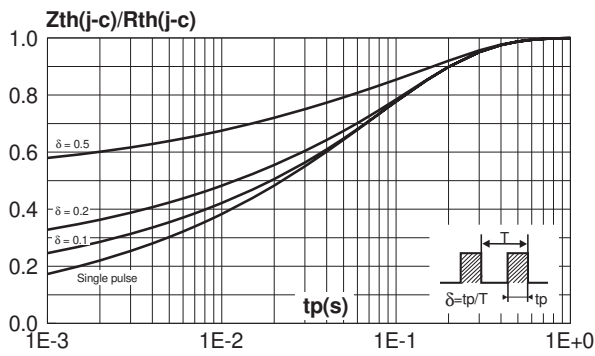


Fig. 6-2: Relative variation of thermal impedance junction to case versus pulse duration (per diode).(TO-220FPAB)

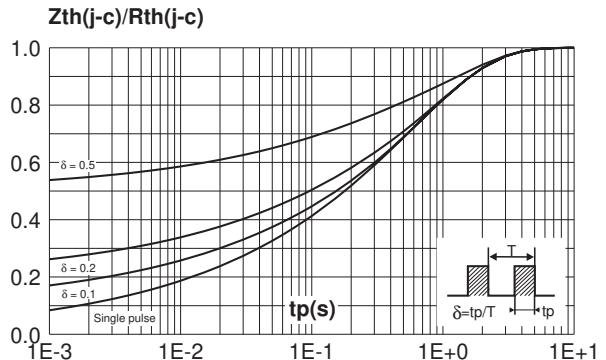


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values, per diode).

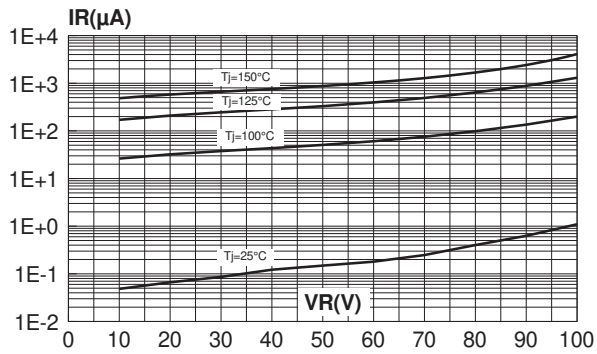


Fig. 8: Junction capacitance versus reverse voltage applied (typical values, per diode).

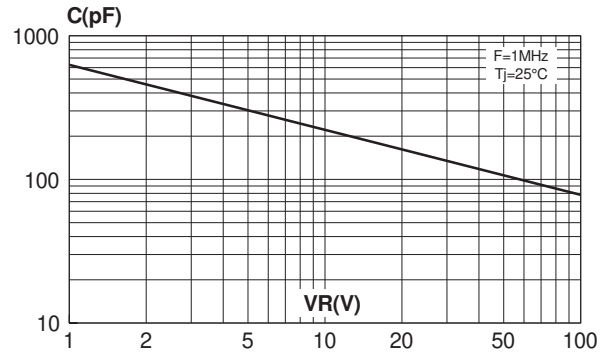


Fig. 9: Forward voltage drop versus forward current (maximum values, per diode).

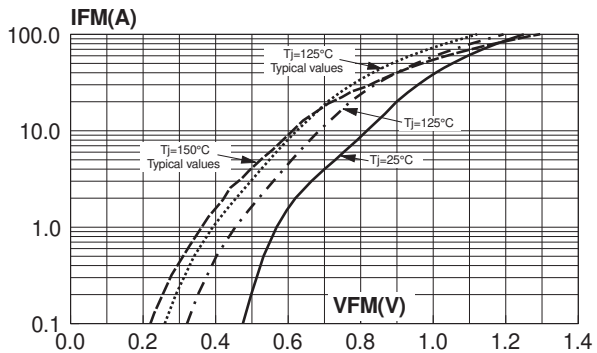
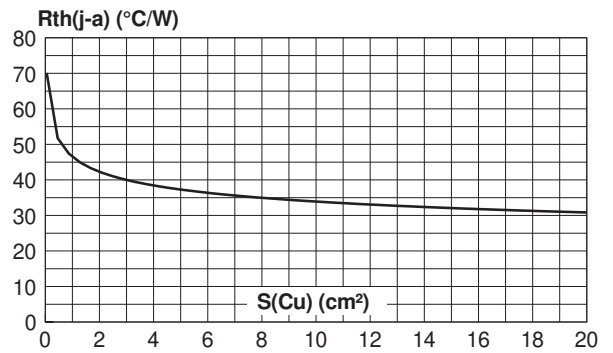
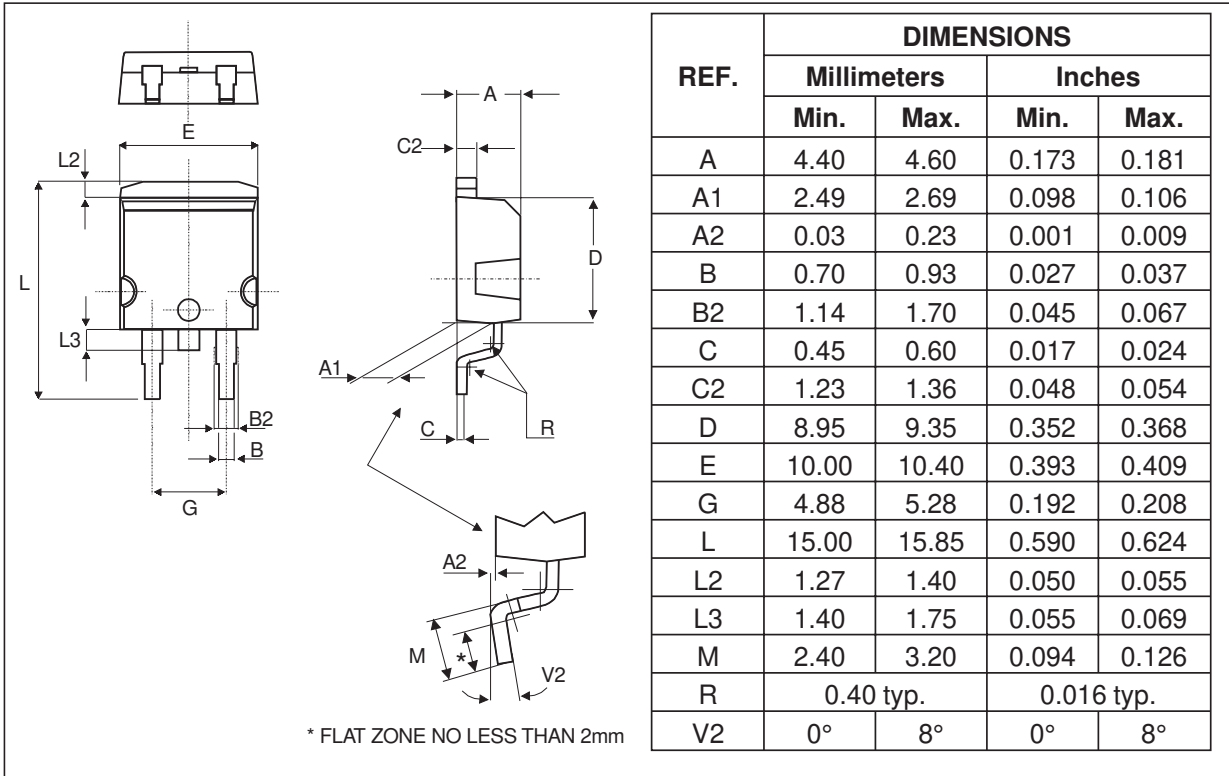


Fig. 10: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35 μm)

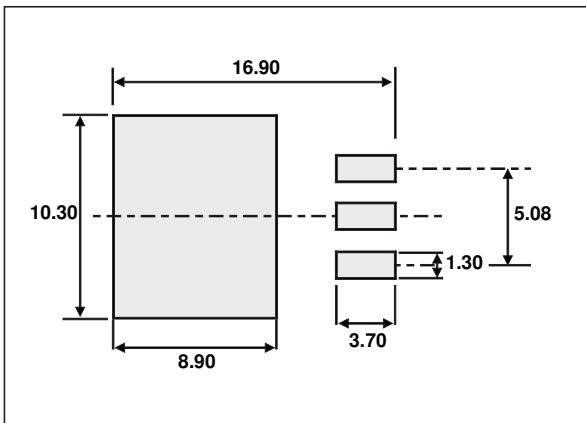


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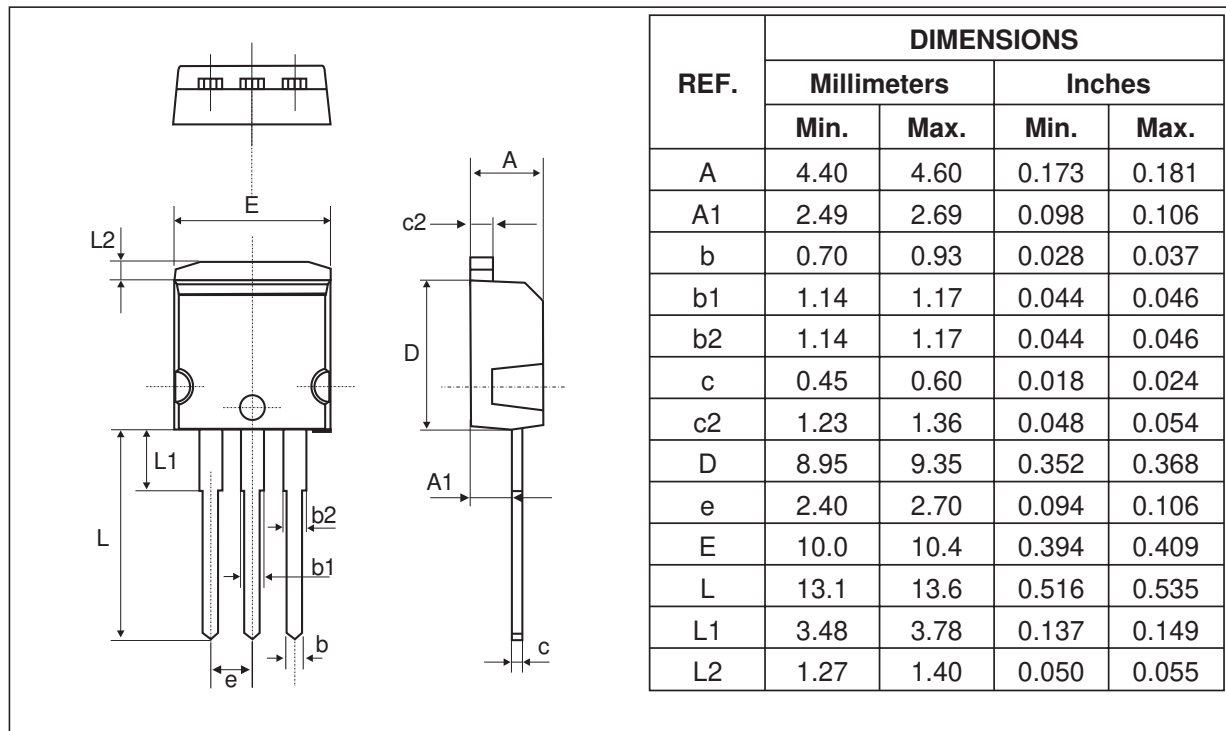
PACKAGE MECHANICAL DATA
D²PAK



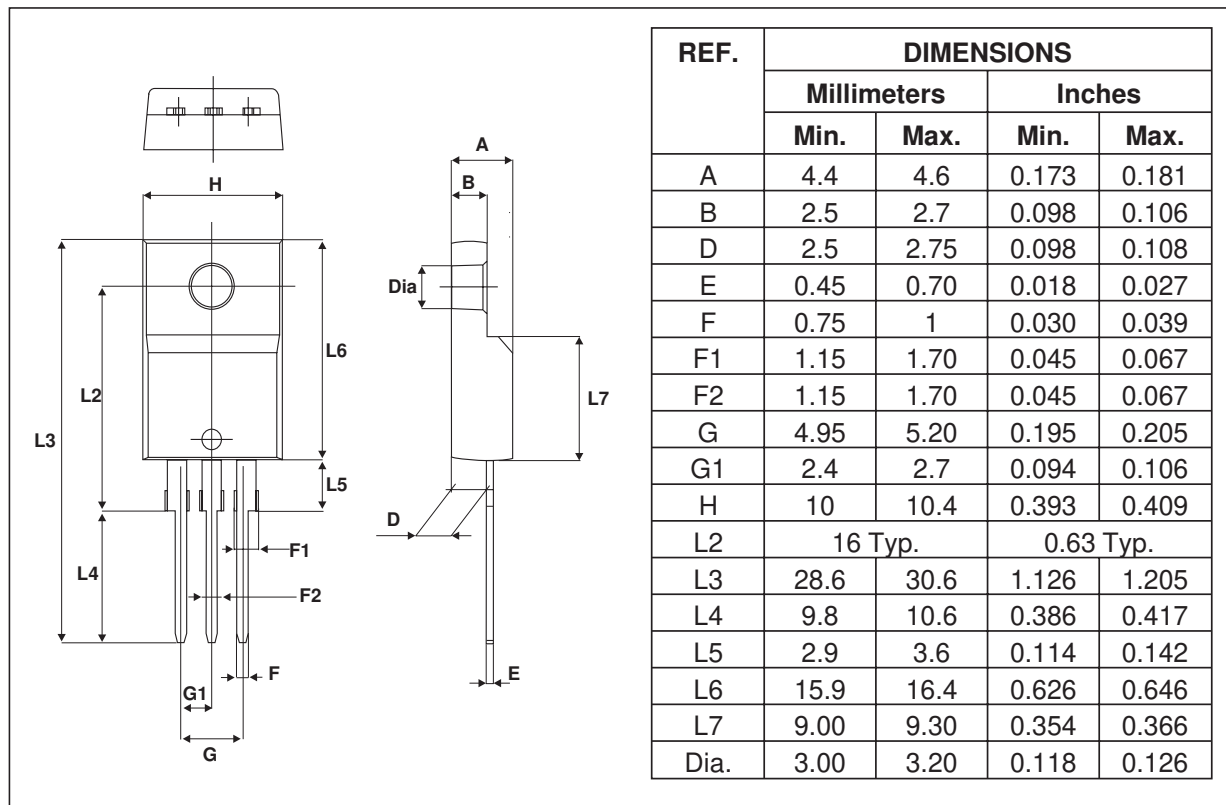
FOOT PRINT in millimeters



PACKAGE MECHANICAL DATA
i²PAK

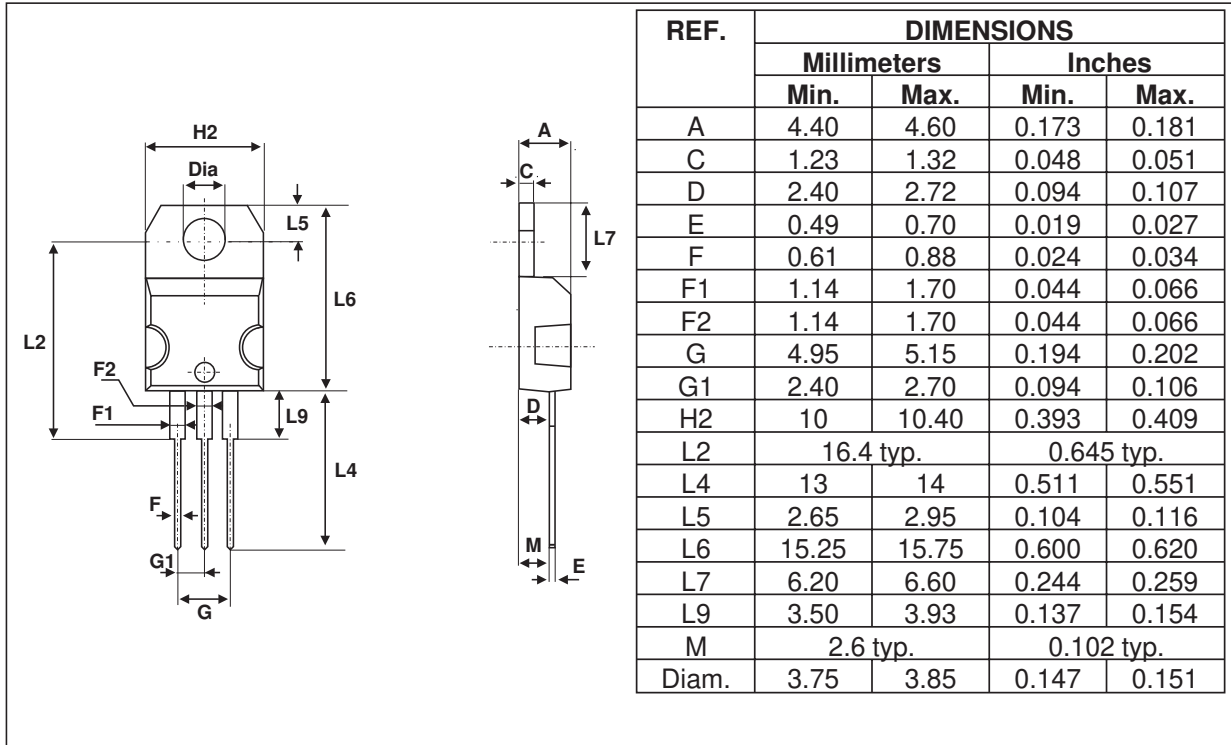


PACKAGE MECHANICAL DATA
TO-220FPAB



STPS10H100CT/CG/CR/CFP

PACKAGE MECHANICAL DATA TO-220AB



- Cooling method: C.
- Recommended torque value: 0.55 m.N
- Maximum torque value 0.70 m.N

| Ordering type | Marking | Package | Weight | Base qty | Delivery mode |
|-----------------|---------------|--------------------|--------|----------|---------------|
| STPS10H100CT | STPS10H100CT | TO-220AB | 2.20g | 50 | Tube |
| STPS10H100CFP | STPS10H100CFP | TO-220FPAB | 2.0 g | 50 | Tube |
| STPS10H100CG | STPS10H100CG | D ² PAK | 1.48g | 50 | Tube |
| STPS10H100CG-TR | STPS10H100CG | D ² PAK | 1.48g | 1000 | Tape and reel |
| STPS10H100CR | STPS10H100CR | I ² PAK | 1.49g | 50 | Tube |

- Epoxy meets UL94,V0

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